



DMT3020LFDB

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
30V	20mΩ @ V _{GS} = 10V	7.7A
	$32m\Omega @ V_{GS} = 4.5V$	6.1A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- **Power Management Functions**

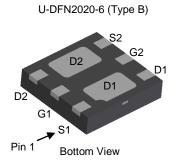
DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

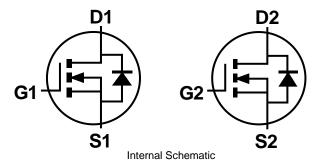
Features and Benefits

- 0.6mm Profile Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: U-DFN2020-6 •
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)





Ordering Information (Note 4)

	Part Number	Case	Packaging			
	DMT3020LFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel			
DMT3020LFDB-13		U-DFN2020-6 (Type B)	10,000/Tape & Reel			
Notes:	1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.					

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



Y2 = Product Type Marking Code $\begin{array}{l} YM = \text{Date Code Marking} \\ YM = \text{Date Code Marking} \\ Y = \text{Year (ex: F = 2018)} \\ M = \text{Month (ex: 9 = September)} \end{array}$

Date Code Key												
Year	201	5	2016		2017	20	18	2019		2020	2	2021
Code	С		D		E	F	-	G		Н		
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2



Y2 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 8 = 2018)

W = Week (ex: a = week 27; z represents week 52 and 53)X = Internal Code (ex: U = Monday)

Date Code Key								
Year	2018	2019	2020	2021	2022	2 2023	2024	2025
Code	8	9	0	1	2	3	4	5
Week	1-26			27-52 53				3
Code	A-Z			A-Z a-z z			<u> </u>	
.								
Internal Code	Sun	Mon	Т	ue	Wed	Thu	Fri	Sat
Code	Т	U	,	V	W	Х	Y	Z



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	30	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +75°C	ID	7.7 6.2	А
Maximum Continuous Body Diode Forward Curre	Is	2	А		
Pulsed Drain Current (380µs Pulse, Duty Cycle =	I _{DM}	50	A		

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	170	°C/W
Total Power Dissipation (Note 6)		PD	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	70	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	Oymbol	WIIII	Typ	Max	Onic	Test condition
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_{D} = 250 \mu A$
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	—	—	1	μA	$V_{DS} = 24V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						÷
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	20	mΩ	$V_{GS} = 10V, I_D = 9.0A$
				32		$V_{GS} = 4.5V, I_D = 7.0A$
Diode Forward Voltage	V _{SD}	—	—	1.0	V	$V_{GS} = 0V, I_{S} = 2A$
DYNAMIC CHARACTERISTICS (Note 8)						F
Input Capacitance	Ciss	—	393	—	pF	
Output Capacitance	Coss	—	173	—	pF	− V _{DS} = 15V, V _{GS} = 0V, − f = 1.0MHz
Reverse Transfer Capacitance	Crss	—	27	—	pF	1 = 1.00012
Gate Resistance	R _G	—	1.1	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = 10V)	Q _G	_	7.0	—	nC	
Total Gate Charge (V _{GS} = 4.5V)	Q_{G}	—	3.6	—	nC	V _{DD} = 15V, I _D = 9A
Gate-Source Charge	Q _{GS}	—	0.9	—	nC	$v_{DD} = 13v, I_D = 9A$
Gate-Drain Charge	Q _{GD}	—	1.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	_	1.8	_	ns	
Turn-On Rise Time	t _R	—	1.9	—	ns	V _{DD} = 15V, V _{GS} = 10V,
Turn-Off Delay Time	t _{D(OFF)}	—	7.5	—	ns	$R_G = 6\Omega, I_D = 9A$
Turn-Off Fall Time	t _F	—	2.4	—	ns	
Reverse Recovery Time	t _{RR}	—	10	—	ns	I _F = 9A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	_	2.6	_	nC	$T_F = 9A$, $u/ut = 100A/\mu S$

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

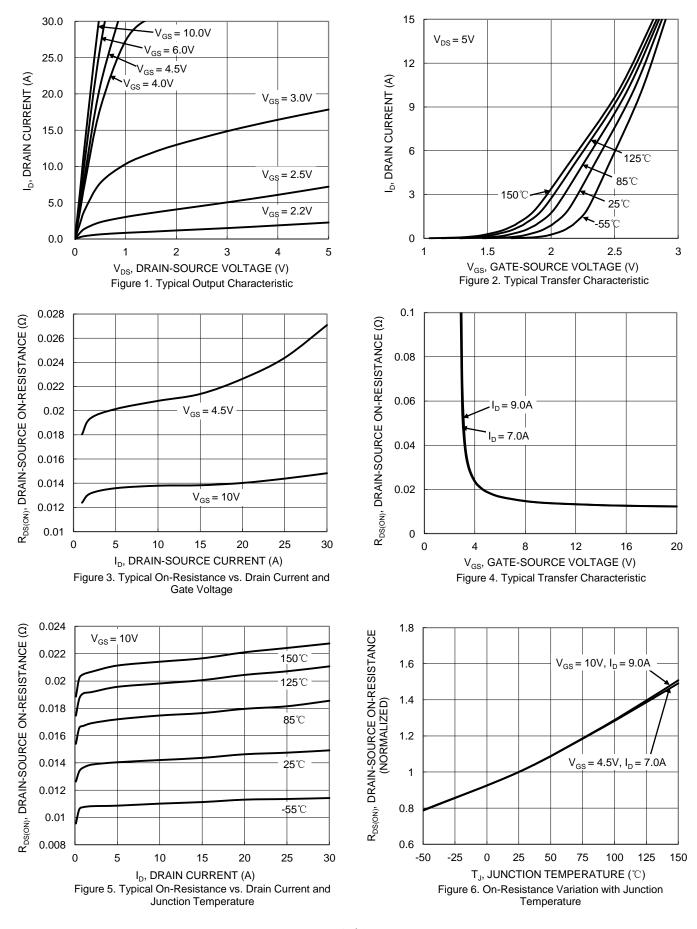
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.



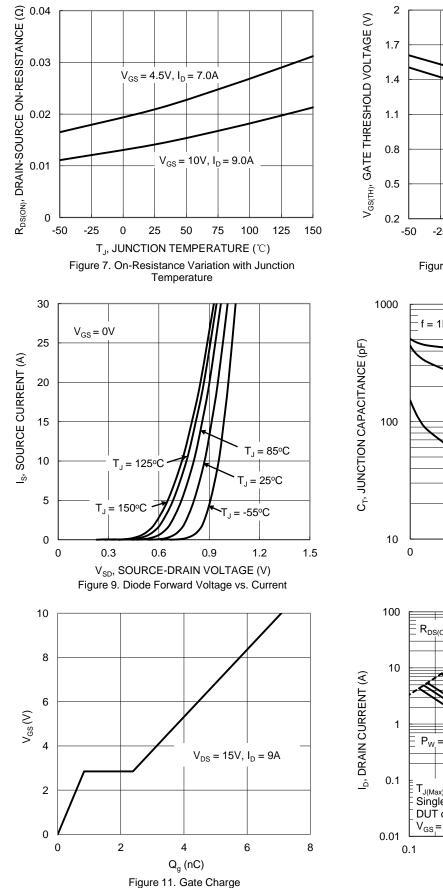
DMT3020LFDB

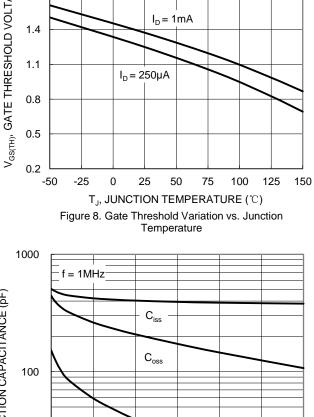


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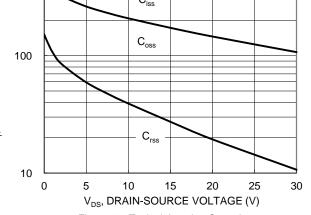
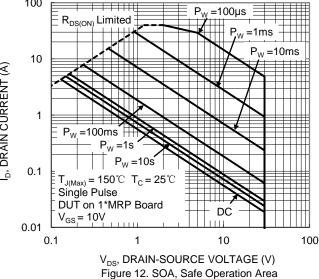
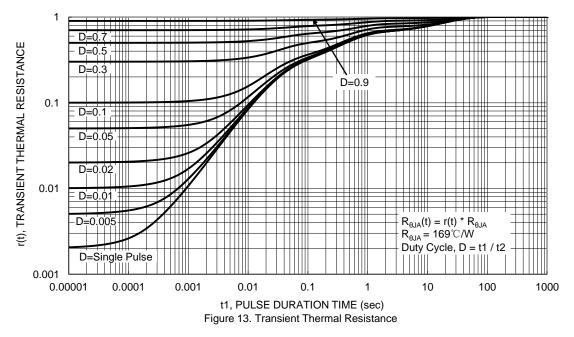


Figure 10. Typical Junction Capacitance



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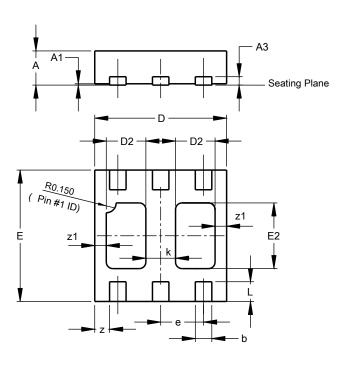






Package Outline Dimensions

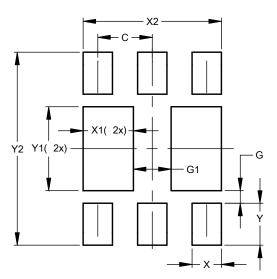
Please see http://www.diodes.com/package-outlines.html for the latest version.



	U-DFN2020-6 Type B								
Dim									
Α	0.545	0.605	0.575						
A1	0.00	0.05	0.02						
A3	-	-	0.13						
b	0.20	0.30	0.25						
D	1.95	2.075	2.00						
D2	0.50	0.70	0.60						
е	-	-	0.65						
Е	1.95	2.075	2.00						
E2	0.90	1.10	1.00						
k	-	-	0.45						
L	0.25	0.35	0.30						
z	-	-	0.225						
z1	-	-	0.175						
All	Dimens	ions in	mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN2020-6 (Type B)

U-DFN2020-6 (Type B)

Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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